

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use several sheets if necessary)

Atty. Docket No.
98095DIV4

Serial No.:

10/008,653

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Applicant Gonzales

Filing Date
November 9, 2001Group
2815

U. S. PATENT DOCUMENTS

Examiner Initial	Document Number	Issue Date	Patentee	Class	Sub- Class	Filing Date
h-v	4,470,852	Sep. 11, 1984	Ellsworth			

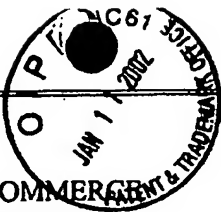
FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

Examiner Initial	Document Number	Public. Date	Country or Patent Office	Class	Sub- Class	Transl Y N

OTHER DOCUMENTS

(Including Author, Title, Date, Relevant Pages, Place of Publication)

h-v			Wolf et al. (Silicon Processing For The VLSI ERA, Volume 1: Process Technology, pp. 397-399, 1986)
Examiner	Date Considered 7/25/02		
EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			



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Atty. Docket No.
98095DIV3Serial No.
10/008,653Applicant
Gonzalez et al.Filing Date
11/9/01

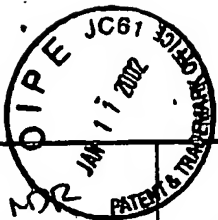
Group 2815

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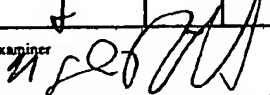
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